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OPTICAL PHENOMENON-ELECTRO-OPTICAL PHENOMENON (OP-[E-OP])-TRANSITION IN n(p)-TYPE DEGENERATE "COMPENSATED" GaAs(1-x)Te(x) -CRYSTALLINE ALLOY (3)

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ABSTRACT

In the $\mathbf{n^+(p^+) - GaAs(1-x)Te(x)}$ $-$ crystalline alloy, $0 \le x \le 1$, x being the concentration, the optical coefficients, and the electrical-and-thermoelectric laws, relations, and various coefficients, enhanced by : (i) our static dielectric constant law, $\varepsilon(r_{d(a)},x)$, $r_{d(a)}$ being the donor (acceptor) d(a)-radius, given in Equations (1a, 1b), (ii) our accurate Fermi energy at $T \ge 0$ K, $E_{Fn(Fp)}(E_{Fno(Fpo)})$, determined in Eq. (11) and accurate with a precision of the order of 2.11×10^{-4} [9], affecting all the expressions of optical, electrical, and thermoelectric coefficients, are now investigated, by basing on our physical model, and Fermi-Dirac distribution function, as those given in our recent works.[1, 2, 3] In the following, for given physical conditions, all the optical coefficients are expressed as functions of the effective photon energy : $E^* \equiv E - E_{gn1(gp1)}$, E and $E_{gn1(gp1)}$, being the photon energy and the optical band gap. Then, some important remarks can be repoted as follows. From our essential optical conductivity model, $\sigma_O(E^*)$, determined in Eq. (18), all the optical, electrical, thermoelectric coefficients are determined, as those given in Equations (19a-19d, 20a-20d). In particular, from the optical phenomenon and electro-optical phenomenon (OP – [E-OP])-transition, obtained for $E = E_{gn1(gp1)} + E_{Fn(Fp)}$, and given in Eq. (15), one observes that the optical conductivity σ_{OT} has a same form with that of the electrical conductivity, σ_{ET}, as those given in Eq. (20a), suggesting thus many important concluding remarks on all the optical, electrical, thermoelectric coefficients at such the (OP and E-OP)-transition, as those given in Equations (20a, 21-31).

KEYWORDS: Optical-and-electrical conductivity, Seebeck coefficient (S), Figure of merit (ZT), First Van-Cong coefficient (VC1), Second Van-Cong coefficient (VC2), Thomson coefficient (Ts), Peltier coefficient (Pt).

INTRODUCTION

In the $\mathbf{n^{+}(p^{+})-GaAs(1-x)Te(x)}$ − crystalline alloy, $0 \leq x \leq 1$, x being the concentration, the optical coefficients, the electrical-and-thermoelectric laws, the relations, and various coefficients, being enhanced by:

(i) our static dielectric constant law, $\varepsilon(r_{d(a)},x)$, $r_{d(a)}$ being the donor (acceptor) d(a)-radius, given in Equations (1a, 1b),

(ii) our accurate Fermi energy, $E_{Fn(Fp)}$, given in Eq. (11) and accurate with a precision of the order of 2.11×10^{-4} [9], affecting all the expressions of optical, electrical, and thermoelectric coefficients ,

(iii)our optical phenomenon and electro-optical phenomenon (OP and E-OP)-transition, given in Eq. (15), and finally

(iv)our optical-and-electrical conductivity models, given in Eq. (18, 20a), are now investigated by basing on our physical model, and Fermi-Dirac distribution function, as those given in our recent works.[1, 2, 3]

It should be noted here that for x=0, these obtained numerical results may be reduced to those given in the n(p)-type degenerate **GaAs-crystal.**[3-13] Then, some important remarks can be repoted as follows.

(1) As observed in Equations (3, 5, 6), the critical impurity density $N_{CDn(CDp)}$, defined by the generalized Mott criterium in the metal-insulator transition (**MIT**), is just the density of electrons (holes), localized in the exponential conduction (valence)-band tail (**EBT**), $N^{EBT}_{CDn(CDp)}$, being obtained with a precision of the order of $\mathbf{2.89 \times 10^{-7}}$, as given in our recent works.[3] Therefore, the effective electron (hole)-density can be defined as: $N^{*} \equiv N - N_{CDn(CDp)} \simeq N - N^{EBT}_{CDn(CDp)}$, N being the total impurity density, as that observed in the compensated crystals.

(2) The ratio of the inverse effective screening length $k_{sn(sp)}$ to Fermi wave number $k_{Fn(kp)}$ at 0 K, $R_{sn(sp)}(N^*)$, defined in Eq. (7), is valid at any N^*.

(3) From Equations (20a, 21-30), for any given x, $r_{d(a)}$ and N (or T), with increasing T (or decreasing N), one obtains: (i) for $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}} \simeq 1.8138$, while the numerical results of the Seebeck coefficient $S_{ET[OT]}$ present a same minimum $(S_{ET[OT]})_{min.}$ $\left(\simeq -1.563 \times 10^{-4} \frac{V}{K}\right)$, those of the figure of merit $ZT_{ET[OT]}$ show a same maxi**mum** $(ZT_{ET[OT]})_{max.} = 1$, (ii) for $\xi_{n(p)} = 1$, the numerical results of $S_{ET[OT]}$, $ZT_{ET[OT]}$, the Mott figure of merit $ZT_{ET[OT]Mott}$, the first Van-Cong coefficient $VC1_{ET[OT]}$, and the Thomson coefficient $Ts_{ET[OT]}$, present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715, 3.290, $1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-4} \frac{V}{K}$, respectively, and finally (iii) for $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}} \simeq 1.8138$, $ZT_{ET[OT]Mott} = 1$, as those given in our recent work.[1] It seems that these same results could represent **a new law in the thermoelectric properties, obtained in the degenerate case ($\xi_{n(p)} \geq 0$).**

(4) Further, our electrical-and-thermoelectric relation is given in Eq. (31) by: $\frac{k_B}{q} \times VC2_{ET[OT]}(N, r_{d(a)}, x, T) \equiv -\frac{\partial S_{ET[OT]}}{\partial \xi_{n(p)}} \times \frac{D_{ET[OT]}(N, r_{d(a)}, x, T)}{\mu_{ET[OT]}(N, r_{d(a)}, x, T)} \left(\frac{V^2}{K}\right)$, $\frac{k_B}{q} = \sqrt{\frac{3 \times L}{\pi^2}}$, according, in this work, to: $VC2_{ET[OT]}(N, r_{d(a)}, x, T) \equiv -\frac{D_{ET[OT]}(N, r_{d(a)}, x, T)}{\mu_{ET[OT]}(N, r_{d(a)}, x, T)} \times 2 \times \frac{ZT_{ET[OT]Mott} \times [1 - ZT_{ET[OT]Mott}]}{[1 + ZT_{ET[OT]Mott}]^2}$ (V), being reduced to: $\frac{D_{ET[OT]}}{\mu_{ET[OT]}}$, $VC1_{ET[OT]}$ and $VC2_{ET[OT]}$, determined respectively in Equations (24, 27, 28). This can be **a new result**.

(5) Finally, for given $[N, r_{d(a)}, x, T]$, all the numerical results of $[\sigma_O(E), \kappa_O(E), \varepsilon_{2O}(E)$, and $\propto_O(E)]$, given in the OP, and those of $[\sigma_E(E), \kappa_E(E), \varepsilon_{2E}(E)$, and $\propto_E(E)]$, given in the E-OP, being determined respectively from Equations (18, 19b-19d], for any E, could thus be used to explain all their corresponding past-or-future experimental results. Therefore, this can also be explained for $\sigma_{ET[OT]}(N, r_{d(a)}, x, T)$, obtained in Eq. (20a) for the (OP – [E-OP])-transition, and their derived electrical-and-thermoelectric results given in Equations (21-31).

In the following, many important sections are presented in order to investigate all the optical coefficients and electrical-and-thermoelectric ones, given in the $n^+(p^+) - CdTe(1-x)S(x)$ $[CdTe(1-x)Se(x)]$ −crystalline alloys at any temperature $T(\geq 0\ K)$.

OUR STATIC DIELECTRIC CONSTANT LAW AND GENERALIZED MOTT CRITERIUM IN THE METAL-INSULATOR TRANSITION

First of all, in the $\mathbf{n^{+}(p^{+})-GaAs(1-x)Te(x)}$ − crystalline alloy, at T=0 K[1, 2, 3], we denote : the donor (acceptor) d(a)-radius by $r_{d(a)}$, the corresponding intrinsic one by: $\mathbf{r_{do(ao)}}$=$\mathbf{r_{As(Ga)}}$, the effective averaged numbers of equivalent conduction (valence)-bands by: $g_{c(v)}$, the unperturbed reduced effective electron (hole) mass in conduction (valence) bands by $m_{c(v)}(x)/m_o$, m_o being the free electron mass, the relative carrier mass by: $m_r(x) \equiv \frac{m_c(x)\times m_v(x)}{m_c(x)+m_v(x)} < m_{c(v)}(x)$, for given x, the unperturbed relative static dielectric constant by: $\varepsilon_o(x)$, and the intrinsic band gap by: $E_{go}(x)$, as those given in the Following Table 1.

Table 1: In the $\boldsymbol{GaAs(1-x)Te(x)}$ − crystalline alloy, the different values of energy-band-structure parameters, for a given x, are given in the following.

In the $\mathbf{GaAs_{1-x}Te_x}$**-crystalline alloy**, in which $r_{do(ao)}$=$r_{As(Ga)}$=**0.118** nm (**0.126** nm), we have[3]: $g_{c(v)}(x) = 1(1)\times x + 1(1)\times(1-x) = 1$, $m_{c(v)}(x)/m_o = 0.209\ (0.4)\times x + 0.066\ (0.291)\times(1-x)$, $\varepsilon_o(x) = 12.3\times x + 13.13\times(1-x)$, $E_{go}(x) = 1.796\times x + 1.52\times(1-x)$.

Here, the effective carrier mass $m^{*}_{n(p)}(x)$ is equal to $m_{c(v)}(x)$. Therefore, we can define the effective donor (acceptor)-ionization energy in absolute values as: $E_{do(ao)}(x) = \frac{13600\times[m^{*}_{n(p)}(x)/m_o]}{[\varepsilon_o(x)]^2}$ meV, and then, the isothermal bulk modulus, by: $B_{do(ao)}(x) \equiv \frac{E_{do(ao)}(x)}{\left(\frac{4\pi}{3}\right)\times\left(r_{do(ao)}\right)^3}$.

Our Static Dielectric Constant Law $\left[m^{*}_{n(p)}(x) \equiv m_{c(v)}(x)\right]$

Here, the changes in all the energy-band-structure parameters, expressed in terms of the effective relative dielectric constant $\varepsilon(r_{d(a)}, x)$, developed as follows.

At $r_{d(a)} = r_{do(ao)}$, the needed boundary conditions are found to be, for the impurity-atom volume V= $(4\pi/3)\times\left(r_{d(a)}\right)^3$, $V_{do(ao)} = (4\pi/3)\times\left(r_{do(ao)}\right)^3$, for the pressure p, $p_o = 0$, and for the deformation potential energy (or the strain energy) α, $\alpha_o = 0$. Further, the two important equations, used to determine the α -variation, $\Delta\,\alpha \equiv \alpha - \alpha_o = \alpha$, are defined by: $\frac{dp}{dV} = -\frac{B}{V}$ and $p = -\frac{d\alpha}{dV}$, giving rise to : $\frac{d}{dV}(\frac{d\alpha}{dV}) = \frac{B}{V}$. Then, by an integration, one gets: $[\Delta\alpha(r_{d(a)},x)]_{n(p)} = B_{do(ao)}(x) \times (V - V_{do(ao)}) \times \ln(\frac{V}{V_{do(ao)}}) = E_{do(ao)}(x) \times \left[\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 - 1\right] \times \ln\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 \geq 0$.

Furthermore, we also showed that, as $r_{d(a)} > r_{do(ao)}$ ($r_{d(a)} < r_{do(ao)}$), the compression (dilatation) gives rise to the increase (the decrease) in the energy gap $E_{gn(gp)}(r_{d(a)},x)$, and the effective donor (acceptor)-ionization energy $E_{d(a)}(r_{d(a)},x)$ in absolute values, obtained in the effective Bohr model, which is represented respectively by : $\pm\,[\Delta\alpha(r_{d(a)},x)]_{n(p)}$,

$$E_{gno(gpo)}(r_{d(a)},x) - E_{go}(x) = E_{d(a)}(r_{d(a)},x) - E_{do(ao)}(x) = E_{do(ao)}(x) \times \left[\left(\frac{\varepsilon_o(x)}{\varepsilon(r_{d(a)})}\right)^2 - 1\right] = +\,[\Delta\alpha(r_{d(a)},x)]_{n(p)},$$

for $r_{d(a)} \geq r_{do(ao)}$, and for $r_{d(a)} \leq r_{do(ao)}$,

$$E_{gno(gpo)}(r_{d(a)},x) - E_{go}(x) = E_{d(a)}(r_{d(a)},x) - E_{do(ao)}(x) = E_{do(ao)}(x) \times \left[\left(\frac{\varepsilon_o(x)}{\varepsilon(r_{d(a)})}\right)^2 - 1\right] = -\,[\Delta\alpha(r_{d(a)},x)]_{n(p)}.$$

Therefore, one obtains the expressions for relative dielectric constant $\varepsilon(r_{d(a)},x)$ and energy band gap $E_{gn(gp)}(r_{d(a)},x)$, as:

(i)-for $r_{d(a)} \geq r_{do(ao)}$, since $\varepsilon(r_{d(a)},x) = \frac{\varepsilon_o(x)}{\sqrt{1+\left[\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 - 1\right] \times \ln\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3}} \leq \varepsilon_o(x)$, being a **new** **$\varepsilon(r_{d(a)},x)$-law**,

$$E_{gno(gpo)}(r_{d(a)},x) - E_{go}(x) = E_{d(a)}(r_{d(a)},x) - E_{do(ao)}(x) = E_{do(ao)}(x) \times \left[\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 - 1\right] \times \ln\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 \geq 0, \qquad (1a)$$

according to the increase in both $E_{gn(gp)}(r_{d(a)},x)$ and $E_{d(a)}(r_{d(a)},x)$, with increasing $r_{d(a)}$ and for a given x, and

(ii)-for $r_{d(a)} \leq r_{do(ao)}$, since $\varepsilon(r_{d(a)},x) = \frac{\varepsilon_o(x)}{\sqrt{1 - \left[\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 - 1\right] \times \ln\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3}} \geq \varepsilon_o(x)$, with a condition, given by: $\left[\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 - 1\right] \times \ln\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 < 1$, being a **new** $\boldsymbol{\varepsilon(r_{d(a)},x)}$**-law**,

$$E_{gno(gpo)}(r_{d(a)},x) - E_{go}(x) = E_{d(a)}(r_{d(a)},x) - E_{do(ao)}(x) = -E_{do(ao)}(x) \times \left[\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 - 1\right] \times \ln\left(\frac{r_{d(a)}}{r_{do(ao)}}\right)^3 \leq 0, \qquad (1b)$$

corresponding to the decrease in both $E_{gno(gpo)}(r_{d(a)},x)$ and $E_{d(a)}(r_{d(a)},x)$, with decreasing $r_{d(a)}$ and for a given x.

It should be noted that, in the following, all the electrical-and-thermoelectric properties strongly depend on this **new** $\boldsymbol{\varepsilon(r_{d(a)},x)}$**-law.**

Furthermore, the effective Bohr radius $a_{Bn(Bp)}(r_{d(a)},x)$ is defined by:

$$a_{Bn(Bp)}(r_{d(a)},x) \equiv \frac{\varepsilon(r_{d(a)},x) \times \hbar^2}{m^*_{n(p)}(x) \times m_o \times q^2} = 0.53 \times 10^{-8}\ \text{cm} \times \frac{\varepsilon(r_{d(a)},x)}{m^*_{n(p)}(x)}. \qquad (2)$$

Generalized Mott Criterium in the MIT $[m^*_{n(p)}(x) \equiv m_{c(v)}(x)]$

Now, it is interesting to remark that the critical total donor (acceptor)-density in the MIT at T=0 K, $N_{CDn(NDp)}(r_{d(a)},x)$, was given by the Mott's criterium, with an empirical parameter, $M_{n(p)}$, as [1, 2, 3]:

$$N_{CDn(CDp)}(r_{d(a)},x)^{1/3} \times a_{Bn(Bp)}(r_{d(a)},x) = M_{n(p)},\quad M_{n(p)} = 0.25, \qquad (3)$$

depending thus on our **new** $\boldsymbol{\varepsilon(r_{d(a)},x)}$**-law**.

This excellent one can be explained from the definition of the reduced effective Wigner-Seitz (**WS**) radius $r_{sn(sp),M}$, in the Mott's criterium, being characteristic of interactions, by :

$$r_{sn(sp),M}(N, r_{d(a)},x) \equiv \left(\frac{3}{4\pi N}\right)^{1/3} \times \frac{1}{a_{Bn(Bp)}(r_{d(a)},x)} = 1.1723 \times 10^8 \times \left(\frac{1}{N}\right)^{1/3} \times \frac{m^*_{n(p)}(x) \times m_o}{\varepsilon(r_{d(a)},x)}, \qquad (4)$$

being equal to, in particular, at N= $N_{CDn(CDp)}(r_{d(a)},x)$: $r_{sn(sp),M}(N_{CDn(CDp)}(r_{d(a)},x), r_{d(a)},x)$= **2.4813963**, for any $(r_{d(a)},x)$-values. Then, from Eq. (4), one also has :

$$N_{CDn(CDp)}(r_{d(a)},x)^{1/3} \times a_{Bn(Bp)}(r_{d(a)},x) = \left(\frac{3}{4\pi}\right)^{\frac{1}{3}} \times \frac{1}{2.4813963} = \mathbf{0.25} = (\mathbf{WS})_{\mathbf{n(p)}} = \mathbf{M}_{\mathbf{n(p)}}, \quad (5)$$

explaining thus the existence of the Mott's criterium.

Furthermore, by using $M_{n(p)} = 0.25$, according to the empirical Heisenberg parameter $\mathcal{H}_{n(p)} = \mathbf{0.47137}$, as those given in our previous work [3], we have also showed that $N_{CDn(CDp)}$ is just **the density of electrons (holes) localized in the exponential conduction (valence)-band tail**, $N^{EBT}_{CDn(CDp)}$, with a precision of the order of 2.89×10^{-7}, respectively.[3]

It shoud be noted that the values of $M_{n(p)}$ and $\mathcal{H}_{n(p)}$ could be chosen so that those of $N_{CDn(CDp)}$ and $N^{EBT}_{CDn(CDp)}$ are found to be in good agreement with their experimental results.

Therefore, the density of electrons (holes) given in parabolic conduction (valence) bands can be defined, as that given in compensated materials:

$N^*(N, r_{d(a)}, x) \equiv N - N_{CDn(NDp)}(r_{d(a)}, x) = N^*$, for a presentation simplicity. (6)

In summary, as observed in Tables 7 and 8 of our previous paper [3], one remarks that, for a given x and an increasing $r_{d(a)}$, $\varepsilon(r_{d(a)}, x)$ decreases, while $E_{gno(gpo)}(r_{d(a)}, x)$, $N_{CDn(NDp)}(r_{d(a)}, x)$ and $N^{EBT}_{CDn(CDp)}(r_{d(a)}, x)$ increase, affecting strongly all the optical properties and the electrical-and-thermoelectric ones, as those observed in following Sections.

PHYSICAL MODEL

In the $n^+(p^+) - \mathbf{GaAs}(1-x)\mathbf{Te}(x)$ – crystalline alloy, the reduced effective Wigner-Seitz (**WS**) radius $r_{sn(sp)}$, characteristic of interactions, being given in Eq. (4), in which N is replaced by N^*, is now defined by:

$\gamma \times r_{sn(sp)}(N^*) \equiv \frac{k^{-1}_{Fn(Fp)}}{a_{Bn(Bp)}} < 1$, $r_{sn(sp)}(N, r_{d(a)}, x) \equiv \left(\frac{3g_{c(v)}}{4\pi N^*}\right)^{1/3} \times \frac{1}{a_{Bn(Bp)}(r_{d(a)}, x)}$, being proportional to $N^{*-1/3}$. Here, $\gamma = (4/9\pi)^{1/3}$, $k_{Fn(Fp)}(N^*) \equiv \left(\frac{3\pi^2 N^*}{g_{c(v)}}\right)^{\frac{1}{3}}$ is the Fermi wave, $g_{c(v)}$ being the effective averaged numbers of equivalent conduction (valence)-bands.

Then, the ratio of the inverse effective screening length $k_{sn(sp)}$ to Fermi wave number $k_{Fn(kp)}$ is defined by:

$$R_{sn(sp)}(N^*) \equiv \frac{k_{sn(sp)}}{k_{Fn(Fp)}} = \frac{k_{Fn(Fp)}^{-1}}{k_{sn(sp)}^{-1}} = R_{snWS(spWS)} + \left[R_{snTF(spTF)} - R_{snWS(spWS)}\right] e^{-r_{sn(sp)}} < 1, \qquad (7)$$

being valid at any N^*.

Here, these ratios, $R_{snTF(spTF)}$ and $R_{snWS(spWS)}$, can be determined as follows.

First, for $N \gg N_{CDn(NDp)}(r_{d(a)}, x)$, according to the **Thomas-Fermi (TF)-approximation**, the ratio $R_{snTF(spTF)}(N^*)$ is reduced to

$$R_{snTF(spTF)}(N^*) \equiv \frac{k_{snTF(spTF)}}{k_{Fn(Fp)}} = \frac{k_{Fn(Fp)}^{-1}}{k_{snTF(spTF)}^{-1}} = \sqrt{\frac{4\gamma r_{sn(sp)}}{\pi}} \ll 1, \qquad (8)$$

being proportional to $N^{*-1/6}$.

Secondly, for $N \ll N_{CDn(NDp)}(r_{d(a)})$, according to the **Wigner-Seitz (WS)-approximation**, the ratio $R_{snWS(snWS)}$ is respectively reduced to

$$R_{sn(sp)WS}(N^*) \equiv \frac{k_{sn(sp)WS}}{k_{Fn}} = 0.5 \times \left(\frac{3}{2\pi} - \gamma \frac{d\left[r_{sn(sp)}^2 \times E_{CE}(N^*)\right]}{dr_{sn(sp)}}\right), \qquad (9a)$$

Where $E_{CE}(N^*)$ is the majority-carrier correlation energy (CE), being determined by:

$$E_{CE}(N^*) = \frac{-0.87553}{0.0908 + r_{sn(sp)}} + \frac{\frac{0.87553}{0.0908 + r_{sn(sp)}} + \left(\frac{2[1-\ln(2)]}{\pi^2}\right) \times \ln(r_{sn(sp)}) - 0.093288}{1 + 0.03847728 \times r_{sn(sp)}^{1.67378876}}.$$

Furthermore, in the highly degenerate case, the physical conditions are found to be given by:

$$\frac{k_{Fn(Fp)}^{-1}}{a_{Bn(Bp)}} < \frac{\eta_{n(p)}}{E_{Fno(Fpo)}} \equiv \frac{1}{A_{n(p)}} < \frac{k_{Fn(Fp)}^{-1}}{k_{sn(sp)}^{-1}} \equiv R_{sn(sp)} < 1, \ \eta_{n(p)}(N^*) \equiv \frac{\sqrt{2\pi \times \left(\frac{N^*}{g_{c(v)}}\right)}}{\varepsilon(r_{d(a)})} \times q^2 k_{sn(sp)}^{-1/2}, \qquad (9b)$$

Which gives: $A_{n(p)}(N^*) = \frac{E_{Fno(Fpo)}(N^*)}{\eta_{n(p)}(N^*)}$, $E_{Fno(Fpo)}(N^*) \equiv \frac{\hbar^2 \times k_{Fn(Fp)}^2(N^*)}{2 \times m_{n(p)}^*(x) \times m_o}$.

BAND GAP NARROWING (BGN) BY N AND BY T

First, the BGN by N is found to be given by[2]:

$$\Delta E_{gn(gp);N}(N^*, r_{d(a)}, x) \simeq a_1 + \frac{\varepsilon_o(x)}{\varepsilon(r_{d(a)}, x)} \times N_r^{\frac{1}{3}} + a_2 \times \frac{\varepsilon_o(x)}{\varepsilon(r_{d(a)}, x)} \times N_r^{\frac{1}{3}} \times \Big(2.503 \times \left[-E_{CE}(r_{sn(sp)})\right] \times r_{sn(sp)}\Big) + a_3 \times \left[\frac{\varepsilon_o(x)}{\varepsilon(r_{d(a)}, x)}\right]^{\frac{5}{4}} \times \sqrt{\frac{m_{v(c)}}{m_{n(p)}^*(x)}} \times N_r^{\frac{1}{4}} + 2a_4 \times \left[\frac{\varepsilon_o(x)}{\varepsilon(r_{d(a)}, x)}\right]^{\frac{1}{2}} \times N_r^{\frac{1}{2}} + 2a_5 \times \left[\frac{\varepsilon_o(x)}{\varepsilon(r_{d(a)}, x)}\right]^{\frac{3}{2}} \times N_r^{\frac{1}{6}}, \ N_r = \frac{N^*}{9.999 \times 10^{17}\,\mathrm{cm}^{-3}}, \qquad (10a).$$

Here, $a_1 = 3.8 \times 10^{-3}(\mathrm{eV})$, $a_2 = 6.5 \times 10^{-4}(\mathrm{eV})$, $a_3 = 2.85 \times 10^{-3}(\mathrm{eV})$, $a_4 = 5.597 \times 10^{-3}(\mathrm{eV})$, and $a_5 = 8.1 \times 10^{-4}(\mathrm{eV})$.

Therefore, at T=0 K and $N^* = 0$, for any $r_{d(a)}$, one gets: $\Delta E_{gn(gp)} = 0$, according to the metal-insulator transition (MIT).

Secondly, one has[2]:

$$\Delta E_{gn(gp);T}(T) = 0.20251 \times \left(\left[1 + \left(\frac{2T}{440.0613\ K} \right)^{2.201} \right]^{\frac{1}{2.201}} - 1 \right). \qquad (10b)$$

FERMI ENERGY AND FERMI-DIRAC DISTRIBUTION FUNCTION

Fermi Energy

Here, for a presentation simplicity, we change all the sign of various parameters, given in the $p^+ -$ **GaAs(1 − x)Te(x)** − crystalline alloy, in order to obtain the same one, as given in the $n^+ -$ **GaAs(1 − x)Te(x)** − crystalline alloy, according to the reduced Fermi energy $E_{Fn(Fp)}$, $\xi_{n(p)}(N, r_{d(a)}, x, T) \equiv \frac{E_{Fn(Fp)}(N, r_{d(a)}, x, T)}{k_B T} > 0 (< 0)$, obtained respectively in the degenerate (non-degenerate) case.

For any $(N, r_{d(a)}, x, T)$, the reduced Fermi energy $\xi_{n(p)}(N, r_{d(a)}, x, T)$ or the Fermi energy $E_{Fn(Fp)}(N, r_{d(a)}, x, T)$, obtained in our previous paper[9], obtained with a precision of the order of 2.11×10^{-4}, is found to be given by:

$$\xi_{n(p)}(u) \equiv \frac{E_{Fn(Fp)}(u)}{k_B T} = \frac{G(u) + Au^B F(u)}{1 + Au^B} \equiv \frac{V(u)}{W(u)},\ A = 0.0005372 \text{ and } B = 4.82842262, \qquad (11)$$

Where u is the reduced electron density, $u(N, r_{d(a)}, x, T) \equiv \frac{N^*}{N_{c(v)}(T,x)}$, $N_{c(v)}(T,x) = 2g_{c(v)} \times \left(\frac{m^*_{n(p)}(x) \times m_o \times k_B T}{2\pi\hbar^2} \right)^{\frac{3}{2}} (\mathrm{cm}^{-3})$, $F(u) = au^{\frac{2}{3}} \left(1 + bu^{-\frac{4}{3}} + cu^{-\frac{8}{3}} \right)^{-\frac{2}{3}}$, $a = [3\sqrt{\pi}/4]^{2/3}$, $b = \frac{1}{8}\left(\frac{\pi}{3}\right)^2$, $c = \frac{62.3739855}{1920}\left(\frac{\pi}{3}\right)^4$, and $G(u) \simeq Ln(u) + 2^{-\frac{3}{2}} \times u \times e^{-du}$; $d = 2^{3/2}\left[\frac{1}{\sqrt{27}} - \frac{3}{16}\right] > 0$.

So, in the non-degenerate case ($u \ll 1$), one has: $E_{Fn(Fp)}(u) = k_B T \times G(u) \simeq k_B T \times Ln(u)$ as $\mathbf{u \longrightarrow 0}$**, the limiting non-degenerate condition**, and in the very degenerate case ($u \gg 1$), one gets: $E_{Fn(Fp)}(u \gg 1) = k_B T \times F(u) = k_B T \times au^{\frac{2}{3}} \left(1 + bu^{-\frac{4}{3}} + cu^{-\frac{8}{3}} \right)^{-\frac{2}{3}} \simeq \frac{\hbar^2 \times k^2_{Fn(Fp)}(N^*)}{2 \times m^*_{n(p)}(x) \times m_o}$

as $\mathbf{u \longrightarrow \infty}$, **the limiting degenerate condition**. In other words, $\xi_{n(p)} \equiv \frac{E_{Fn(Fp)}}{k_B T}$ is accurate, and it also verifies the correct limiting conditions.

In particular, as $T \rightarrow 0\ K$, since $u^{-1} \rightarrow 0$, Eq. (11) is reduced to: $E_{Fno(Fpo)}(N^*) \equiv \frac{\hbar^2 \times k^2_{Fn(Fp)}(N^*)}{2 \times m^*_{n(p)}(x) \times m_o}$, being proportional to $(N^*)^{2/3}$, and also equal to 0 at $N^* = 0$, according to the MIT and noting that $E_{Fno(Fpo)}(m_r(x)) > E_{Fno(Fpo)}\left(m_{c(v)}(x)\right)$ since $m_r(x) < m_{c(v)}(x)$ for given x.

In the following, it should be noted that all the optical and electrical-and-thermoelectric properties strongly depend on such the accurate expression of $\xi_{n(p)}(N, r_{d(a)}, x, T)$.[9]

Fermi-Dirac Distribution Function (FDDF)

The Fermi-Dirac distribution function (FDDF) is given by: $f(E) \equiv (1 + e^{\gamma})^{-1}$, $\gamma \equiv (E - E_{Fn(Fp)})/(k_B T)$.

So, the average of E^p, calculated using the FDDF-method, as developed in our previous works [1, 6] is found to be given by:

$$\langle E^p \rangle_{FDDF} \equiv G_p(E_{Fn(Fp)}) \times E^p_{Fn(Fp)} \equiv \int_{-\infty}^{\infty} E^p \times \left(-\frac{\partial f}{\partial E}\right) dE, \quad -\frac{\partial f}{\partial E} = \frac{1}{k_B T} \times \frac{e^{\gamma}}{(1+e^{\gamma})^2}.$$

Further, one notes that, at 0 K, $-\frac{\partial f}{\partial E} = \delta(E - E_{Fno(Fpo)})$, $\delta(E - E_{Fno(Fpo)})$ being the Dirac delta (δ)-function. Therefore, $G_p(E_{Fno(Fpo)}) = 1$.

Then, at low T, by a variable change $\gamma \equiv (E - E_{Fn(Fp)})/(k_B T)$, one has:

$$G_p(E_{Fn(Fp)}) \equiv 1 + E^{-p}_{Fn(Fp)} \times \int_{-\infty}^{\infty} \frac{e^{\gamma}}{(1+e^{\gamma})^2} \times (k_B T\gamma + E_{Fn(Fp)})^p d\gamma = 1 + \sum_{\mu=1,2,\dots}^{p} C_p^{\beta} \times (k_B T)^{\beta} \times E^{-\beta}_{Fn(Fp)} \times I_{\beta} \quad ,$$

Where $C_p^{\beta} \equiv p(p-1)\dots(p-\beta+1)/\beta!$ and the integral I_β is given by:

$I_\beta = \int_{-\infty}^{\infty} \frac{\gamma^{\beta} \times e^{\gamma}}{(1+e^{\gamma})^2} d\gamma = \int_{-\infty}^{\infty} \frac{\gamma^{\beta}}{(e^{\gamma/2}+e^{-\gamma/2})^2} d\gamma$, vanishing for old values of β. Then, for even values of $\beta = 2n$, with n=1, 2, …, one obtains:

$$I_{2n} = 2\int_0^{\infty} \frac{\gamma^{2n} \times e^{\gamma}}{(1+e^{\gamma})^2} d\gamma \, .$$

Now, using an identity $(1+e^{\gamma})^{-2} \equiv \sum_{s=1}^{\infty}(-1)^{s+1}s \times e^{\gamma(s-1)}$, a variable change: $s\gamma = -t$, the Gamma function: $\int_0^{\infty} t^{2n}e^{-t}\,dt \equiv \Gamma(2n+1) = (2n)!$, and also the definition of the Riemann's zeta function: $\zeta(2n) \equiv 2^{2n-1}\pi^{2n}|B_{2n}|/(2n)!$, B_{2n} being the Bernoulli numbers, one finally gets: $I_{2n} = (2^{2n}-2) \times \pi^{2n} \times |B_{2n}|$. So, from above Eq. of $\langle E^{p}\rangle_{FDDF}$, we get in the degenerate case the following ratio:

$$G_p\left(E_{Fn(Fp)}\right) \equiv \frac{\langle E^{p}\rangle_{FDDF}}{E^{p}_{Fn(Fp)}} = 1 + \sum_{n=1}^{p} \frac{p(p-1)\dots(p-2n+1)}{(2n)!} \times (2^{2n}-2) \times |B_{2n}| \times y^{2n} \equiv G_{p\geq1}(y), \qquad (12)$$

Where $y \equiv \frac{\pi}{\xi_{n(p)}(N^{*},T)} = \frac{\pi k_B T}{E_{Fn(Fp)}(N^{*},T)}$, noting that $G_{p=1}(y \equiv \frac{\pi k_B T}{E_{Fn(Fp)}} = \frac{\pi}{\xi_{n(p)}}) = 1$, and as T→ 0 K, $G_{p>1}(y \to 0) \to 1$.

Then, some usual results of $G_{p\geq1}(y)$ are given in the following Table 2, being needed to determine all the following optical and electrical-and-thermoelectric properties.

Table 2: Expressions for $G_{p>1}(y \equiv \frac{\pi}{\xi_{n(p)}})$, due to the Fermi-Dirac distribution function, are used to determine the electrical-and-thermoelectric coefficients.

$G_{3/2}(y)$	$G_2(y)$	$G_{5/2}(y)$	$G_3(y)$	$G_{7/2}(y)$	$G_4(y)$	$G_{9/2}(y)$
$\left(1+\frac{y^2}{8}+\frac{7y^4}{640}\right)$	$\left(1+\frac{y^2}{3}\right)$	$\left(1+\frac{5y^2}{8}-\frac{7y^4}{384}\right)$	$(1+y^2)$	$\left(1+\frac{35y^2}{24}+\frac{49y^4}{384}\right)$	$\left(1+2y^2+\frac{7y^4}{15}\right)$	$\left(1+\frac{21y^2}{8}+\frac{147y^4}{128}\right)$

OPTICAL-AND-ELECTRICAL PROPERTIES

Optical Phenomenon – Electro-Optical Phenomenon (OP – [E-OP])-Transition $[m^{*}_{n(p)}(x) \equiv m_r(x)[m_{c(v)}(x)]]$

First off on, for a presentation simplicity, we change all the sign of various parameters, given in the $p^{+} -$ $\mathbf{GaAs(1-x)Te(x)}$ $-$ crystalline alloy, in order to obtain the same one, as given in the $n^{+} -$ $\mathbf{GaAs(1-x)Te(x)}$ $-$ crystalline alloy, according to the reduced Fermi energy $E_{Fn(Fp)}$, $\xi_{n(p)}(N, r_{d(a)}, x, T) \equiv \frac{E_{Fn(Fp)}(N, r_{d(a)}, x, T)}{k_B T} > 0 (< 0)$, obtained respectively in the degenerate (non-degenerate) case, giving: $E_{Fno(Fpo)} \equiv E_{Fn(Fp)}(N, r_{d(a)}, x, T = 0)$.

Then, in the $n^{+}(p^{+}) -$ $\mathbf{GaAs(1-x)Te(x)}$ $-$ crystalline alloy, and for the temperature T(K), One has:

(i) in the electrical phenomenon (EP), the reduced band gap is defined by:

$$E_{gn2(gp2)} \equiv E_{c(v)} - E_{vo(co)} = E_{gni(gpi)} - \Delta E_{gn(gp);N}(N^*) - \Delta E_{gn(gp);T}(T), \qquad (13)$$

Where $E_{gni(gpi)}$ is the intrinsic bang gap, $\Delta E_{gn(gp)}(N^*)$ and $\Delta E_{gn(gp)}(T)$ are respectively the reduced band gaps, due to the N^*-and-T effects, as those determined in Equations (10a, 10b), and

(ii) in the optical phenomenon (OP), the photon energy is defined by: $E \equiv \hbar\omega$, and the optical band gap by: $E_{gn1(gp1)} \equiv E_{gn2(gp2)} + E_{Fn(Fp)}$.

Therefore, for $E \geq E_{gn1(gp1)}$, the effective photon energy E^* is found to be given by:

$$E^* \equiv E - E_{gn1(gp1)} = E - \left(E_{gn2(gp2)} + E_{Fn(Fp)}\right) \geq 0. \qquad (14)$$

From above Equations, the (OP $-$ E-OP)-transition means that:

$E^* \equiv [E - E_{gn1(gp1)}]$, given in the OP, in which $E = [E_{gn1(gp1)} + E_{Fn(Fp)}]$, is reduced in the E-OP, in which $E = [E_{gn1(gp1)} + E_{Fn(Fp)}]$ and $m_r(x)$ are now replaced by $E = [E_{gn2(gp2)} + E_{Fn(Fp)}]$ and $m_{c(v)}(x)$, to: $E^* \equiv E - E_{gn2(gp2)} = E_{Fn(Fp)}$, and reciprocally, noting that $E_{Fn(Fp)}(m_r(x)) > E_{Fn(Fp)}\left(m_{c(v)}(x)\right)$ since $m_r(x) < m_{c(v)}(x)$, for given x. (15)

Eq. (15) thus shows that, in both OP and E-OP, the Fermi energy-level penetrations into conduction (valence)-bands, observed in the $n^+(p^+)-$ type degenerate $\mathbf{GaAs(1-x)Te(x)}$ $-$ crystalline alloy, $E_{Fn(Fp)}$, are well defined, noting that at this discontinuous (OP $-$ E-0P)-transition: $E_{Fn(Fp)}(m_r(x)) > E_{Fn(Fp)}\left(m_{c(v)}(x)\right)$, according to the discontinuous case.

Optical Coefficients

The optical properties for any medium, defined in the OP and E-OP, respectively, can be described by the complex refraction: $\mathbb{N}_{O[E]} \equiv n_{O[E]} - i\kappa_{O[E]}$, $n_{O[E]}$ and $\kappa_{O[E]}$ being the refraction index and the extinction coefficient, the complex dielectric function: $\mathcal{E}_{O[E]} = \varepsilon_{1O[1E]} - i\varepsilon_{2O[2E]}$, where $i^2 = -1$, and $\mathcal{E}_{O[E]} = \mathbb{N}_{O[E]}{}^2$. Further, if denoting the normal-incidence reflectance and the optical absorption by $R_{O[E]}$ and $\propto_{O[E]}$, and the joint density of states by:

$$\mathrm{JDOS}_{n(p)O[E]}(E) \equiv \frac{1}{2\pi^2} \times \left(\frac{2m^*_{n(p)}(x)}{\hbar^2}\right)^{3/2} \times \left[\frac{E - E_{gn1(gp1)}}{E - [E_{gn1(gp1)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2 \times \sqrt{E_{Fno(Fpo)}} \,,$$

and $F_{O[E]}(E) \equiv \frac{\hbar q^2 \times |v(E)|^2}{n(E) \times cE \times \varepsilon_{\text{free space}}}$, one gets[2]:

$$\propto_{O[E]}(E) = JDOS_{n(p)O[E]}(E) \times F_{O[E]}(E) = \frac{E \times \varepsilon_{2O[2E]}(E)}{\hbar c n_{O[E]}(E)} = \frac{2E \times \kappa_{O[E]}(E)}{\hbar c}$$

$$= \frac{4\pi\sigma_{O[E]}(E)}{c n_{O[E]}(E) \times \varepsilon_{\text{free space}}},$$

$$\propto_{O[E]}(E) = JDOS_{n(p)O[E]}(E) \times F_{O[E]}(E) = \frac{E \times \varepsilon_{2O[2E]}(E)}{\hbar c n_{O[E]}(E)} = \frac{2E \times \kappa_{O[E]}(E)}{\hbar c} = \frac{4\pi\,\sigma_{O[E]}(E)}{c n_{O[E]}(E) \times \varepsilon_{\text{free space}}}$$

$$\varepsilon_{1O[1E]}(E) \equiv {n_{O[E]}}^2 - {\kappa_{O[E]}}^2,\ \varepsilon_{2O[2E]}(E) \equiv 2\kappa_{O[E]} n_{O[E]},\ \text{and}\ R_{O[E]}(E) \equiv \frac{[n_{O[E]}-1]^2 + {\kappa_{O[E]}}^2}{[n_{O[E]}+1]^2 + {\kappa_{O[E]}}^2}. \quad (16)$$

It should be noted that, such the above joint density of states yeilds: (i) as $E = E_{gn1(gp1)}(T)$, $JDOS_{n(p)O[E]}(E) = 0$, and (ii) as $E \to \infty$, $JDOS_{n(p)O[E]}(E) \to \frac{1}{2\pi^2} \times \left(\frac{2m^*_{n(p)}(x)}{\hbar^2}\right)^{3/2} \times \sqrt{E_{Fno(Fpo)}}$. Further, $\varepsilon_{\text{free space}}$ is the permittivity of the free space, -q is the charge of the electron, $|v_{O[E]}(E)|$ is the matrix elements of the velocity operator between valence (conduction)-and-conduction (valence) bands, and the refraction index $n_{O[E]}$ is found to be defined by[2]:

$$n_{O[E]}(E,\ r_{d(a)}) \equiv n_\infty(r_{d(a)}) + \sum_{i=1}^{4} \frac{B_{oi}E + C_{oi}}{E^2 - B_1 E + C_i} \to n_\infty(r_{d(a)}),\ \text{as}\ E \to \infty. \quad (17)$$

Now, the optical [electrical] conductivity $\sigma_{O[E]}$ can be defined and expressed in terms of the kinetic energy of the electron (hole), $E_k \equiv \frac{\hbar^2 \times k^2}{2 \times m^*_{n(p)}(x) \times m_o}$, k being the wave number, as:

$\sigma_{O[E]}(k) \equiv \frac{q^2 \times k}{\pi \times \hbar} \times \frac{k}{k_{sn(sp)}} \times [k \times a_{Bn(Bp)}] \times \left(\frac{E_k}{\eta_{n(p)}}\right)^{1/2}$, which is thus proportional to ${E_k}^2$.

Then, we obtain: $\langle E^2 \rangle_{FDDF} \equiv G_2\left(y = \frac{\pi k_B T}{E_{Fn(Fp)}}\right) \times E^2_{Fn(Fp)}$, and $G_2(y) = \left(1 + \frac{y^2}{3}\right) \equiv G_2(N, r_{d(a)}, x, T)$, with $y \equiv \frac{\pi}{\xi_{n(p)}}$, $\xi_{n(p)} = \xi_{n(p)}(N, r_{d(a)}, x, T)$ for a presentation simplicity. Therefore, from above equations (16, 17), if denoting the function $H(N, r_{d(a)}, x, T)$ by:

$$H(N, r_{d(a)}, x, T) = \left[\frac{k_{Fn(Fp)}(N^*)}{R_{sn(sp)}(N^*)} \times [k_{Fn(Fp)}(N^*) \times a_{Bn(Bp)}(r_{d(a)}, x)] \times \sqrt{A_{n(p)}(N^*) = \frac{E_{Fno(Fpo)}(N^*)}{\eta_{n(p)}(N^*)}}\right] \times G_2(N, r_{d(a)}, x, T),$$

Where $R_{sn(sp)}(N^*) \equiv \frac{k_{sn(sp)}}{k_{Fn(Fp)}}$, which is proportional to $E^2_{Fno(Fpo)}$, for given $(N, r_{d(a)}, x, T)$-physical conditions, our optical [electrical] conductivity model can thus be assumed to be:

$$\sigma_O(N, r_{d(a)}, x, T, E) = \frac{q^2}{\pi\times\hbar} \times H(N, r_{d(a)}, x, T) \times \left[\frac{E - E_{gn1(gp1)}}{E - [E_{gn1(gp1)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2 \left(\frac{1}{\text{ohm}\times\text{cm}}\right), \text{ and } \sigma_E(N, r_{d(a)}, x, T, E) = \frac{q^2}{\pi\times\hbar} \times H(N, r_{d(a)}, x, T) \times \left[\frac{E - E_{gn2(gp2)}}{E - [E_{gn2(gp2)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2 \left(\frac{1}{\text{ohm}\times\text{cm}}\right), \quad (18)$$

Where $\frac{q^2}{\pi\times\hbar} = 7.7480735 \times 10^{-5}\ \text{ohm}^{-1}$. It should be noted here that:

(i) $\sigma_{O[E]}(E = E_{gn1(gp1)}[E_{gn2(gp2)}]) = 0$, and $\sigma_{O[E]}(E \to \infty) = \frac{q^2}{\pi\times\hbar} \times H(N, r_{d(a)}, x, T) = \text{Constant}$ for given $(N, r_{d(a)}, x, T)$ −physical conditions, and

(ii) as $T \to 0\ K$ and $N^* = 0$ [or $E_{Fno(Fpo)}(N^*)] = 0$, according to: $H(N, r_{d(a)}, x, T) = 0$, and for a given E, $[E - E_{gn1(gp1)}] = [E - E_{gni(gpi)}]$=Constant, then from Equations (16-18), $n_{O[E]}$ (E)= Constant, $\sigma_{O[E]}(E) = 0$, $\kappa_{O[E]}(E) = 0$, $\varepsilon_{1O[1E]}(E) = (n_\infty)^2 = \text{Constant}$, $\varepsilon_{2O[2E]}(E) = 0$, and $\propto_{O[E]}(E) = 0$, according to the metal-insulator transition (MIT).

This result (18) should be new, in comparison with that, obtained from an improved Forouhi-Bloomer parameterization, as given in our previous work.[2]

Using Equations (16-18), one obtains all the analytically results, due to the optical phenomenon (OP) as: $[\sigma_0(E), \kappa_O(E), \varepsilon_{2O}(E)$, and $\propto_O(E)]$, and to the electro-optical phenomenon ([E-OP]) as: $[\sigma_E(E), \kappa_E(E), \varepsilon_{2,E}(E)$, and $\propto_E(E)]$,

$$\frac{|v(E)|^2}{E} = \frac{8\pi^2\hbar}{(2m_r)^{\frac{3}{2}}\times\sqrt{\eta_{n(p)}}} \times \left[\frac{k_{Fn(Fp)}(N^*)}{R_{sn(sp)}(N^*)} \times [k_{Fn(Fp)}(N^*) \times a_{Bn(Bp)}(r_{d(a)}, x)]\right] \times G_2(N, r_{d(a)}, x, T), \quad (19a)$$

$$\kappa_O(E) = \frac{2q^2}{n(E)\times\varepsilon_{\text{free space}}\times E} \times H(N, r_{d(a)}, x, T) \times \left[\frac{E - E_{gn1(gp1)}}{E - [E_{gn1(gp1)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2 \quad \text{and}$$

$$\kappa_E(E) = \frac{2q^2}{n(E)\times\varepsilon_{\text{free space}}\times E} \times H(N, r_{d(a)}, x, T) \times \left[\frac{E - E_{gn2(gp2)}}{E - [E_{gn2(gp2)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2, \quad (19b)$$

Which gives: $\kappa[\kappa_E](E = E_{gn1(gp1)}[E_{gn2(gp2)}]) = 0$, and $\kappa[\kappa_E](E \to \infty) \to 0$, as those given in Ref.[2],

$$\varepsilon_{2O}(E) = \frac{4q^2}{\varepsilon_{\text{free space}}\times E} \times H(N, r_{d(a)}, x, T) \times \left[\frac{E - E_{gn1(gp1)}}{E - [E_{gn1(gp1)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2 \quad \text{and}$$

$$\varepsilon_{2E}(E) = \frac{4q^2}{\varepsilon_{\text{free space}} \times E} \times H\left(N, r_{d(a)}, x, T\right) \times \left[\frac{E - E_{gn2(gp2)}}{E - [E_{gn2(gp2)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2, \qquad (19c)$$

Which gives: $\varepsilon_{2[2E]}\left(E = E_{gn1(gp1)}[E_{gn2(gp2)}]\right) = 0$, and $\varepsilon_{\varepsilon_{2[2E]}}(E \to \infty) \to 0$, as those given in Ref. [2], and

$\propto_O (E) =$
$\frac{4q^2}{\hbar cn(E) \times \varepsilon_{\text{free space}}} \times H\left(N, r_{d(a)}, x, T\right) \times \left[\frac{E - E_{gn1(gp1)}}{E - [E_{gn1(gp1)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2 \ (cm^{-1})$ and

$$\propto_E (E) = \frac{4q^2}{\hbar cn(E) \times \varepsilon_{\text{free space}}} \times H\left(N, r_{d(a)}, x, T\right) \times \left[\frac{E - E_{gn2(gp2)}}{E - [E_{gn2(gp2)} + E_{Fn(Fp)} - E_{Fno(Fpo)}]}\right]^2 \ (cm^{-1}), \qquad (19d)$$

Which gives: $\propto_O [\propto_E]\left(E = E_{gn1(gp1)}[E_{gn2(gp2)}]\right) = 0$, and

$\propto_O [\propto_E](E \to \infty) = \frac{4q^2}{\hbar cn_\infty \times \varepsilon_{\text{free space}}} \times H\left(N, r_{d(a)}, x, T\right) = \text{Constant}$, as those given in Ref.[2]

Using the (OP – [E-OP]) transition, given in Eq. (15), at $E = E_{gn1(gp1)} + E_{Fn(Fp)}$, the optical conductivity, σ_{OT}, given in Eq. (18), in which $m^*_{n(p)}(x) = m_r(x)$ is now replaced by $m_{c(v)}(x)$, has a same form with that of the electrical conductivity, σ_{ET}, given in our recent work [1], for such the (OP – [E-OP])- transition. So, from Equations (18, 19b, 19c, 19d), and for $E = E_{gn1(gp1)}[E_{gn2(gp2)}] + E_{Fn(Fp)}$, ones obtains respectively, as:

$$\sigma_{OT}(N, r_{d(a)}, x, T, E) = \frac{q^2}{\pi \times \hbar} \times H\left(N, r_{d(a)}, x, T\right) \times \left(\frac{E_{Fn(Fp)}}{E_{Fno(Fpo)}}\right)^2 \left(\frac{1}{ohm \times cm}\right),$$

Having the same form with that of $\sigma_{ET}\left(N, r_{d(a)}, x, T\right)$ [1], as:

$$\sigma_{ET}(N, r_{d(a)}, x, T, E) = \frac{q^2}{\pi \times \hbar} \times H\left(N, r_{d(a)}, x, T\right) \times \left(\frac{E_{Fn(Fp)}}{E_{Fno(Fpo)}}\right)^2 \left(\frac{1}{ohm \times cm}\right), \qquad (20a)$$

$$\kappa_{OT}(N, r_{d(a)}, x, T, E) = \frac{2q^2}{n(E) \times \varepsilon_{\text{free space}} \times (E_{gn1(gp1)} + E_{Fn(Fp)})} \times H\left(N, r_{d(a)}, x, T\right) \times \left(\frac{E_{Fn(Fp)}}{E_{Fno(Fpo)}}\right)^2 \text{ and}$$

$$\kappa_{ET}(N, r_{d(a)}, x, T, E) = \frac{2q^2}{n(E) \times \varepsilon_{\text{free space}} \times (E_{gn2(gp2)} + E_{Fn(Fp)})} \times H\left(N, r_{d(a)}, x, T\right) \times \left(\frac{E_{Fn(Fp)}}{E_{Fno(Fpo)}}\right)^2, \qquad (20b)$$

$$\varepsilon_{2OT}(N, r_{d(a)}, x, T, E) = \frac{4q^2}{\varepsilon_{\text{free space}} \times (E_{gn1(gp1)} + E_{Fn(Fp)})} \times H\left(N, r_{d(a)}, x, T\right) \times \left(\frac{E_{Fn(Fp)}}{E_{Fno(Fpo)}}\right)^2 \text{ and}$$

$$\varepsilon_{2ET}(N, r_{d(a)}, x, T, E) = \frac{4q^2}{\varepsilon_{\text{free space}} \times (E_{gn2(gp2)} + E_{Fn(Fp)})} \times H\left(N, r_{d(a)}, x, T\right) \times \left(\frac{E_{Fn(Fp)}}{E_{Fno(Fpo)}}\right)^2 \qquad (20c)$$

$$\propto_{OT}\left(N, r_{d(a)}, x, T, E\right) = \frac{4q^2}{\hbar c n(E)\times\varepsilon_{free\ space}} \times H\left(N, r_{d(a)}, x, T\right) \times \left(\frac{E_{Fn(Fp)}}{E_{Fno(Fpo)}}\right)^2 \quad (cm^{-1}) \quad \text{and}$$

$$\propto_{ET}\left(N, r_{d(a)}, x, T, E\right) = \frac{4q^2}{\hbar c n(E)\times\varepsilon_{free\ space}} \times H\left(N, r_{d(a)}, x, T\right) \times \left(\frac{E_{Fn(Fp)}}{E_{Fno(Fpo)}}\right)^2 \quad (cm^{-1}). \qquad (20d)$$

One notes here that (i) the electrical conductivity $\sigma_E(N, r_{d(a)}, x, T)$, given in Eq. (2a), is an essential result, being used to determine the following electrical-and-thermoelectric coefficients, and (ii) as noted in Eq. (15), at this discontinuous (OP – [E-OP])- transition, given in the discontinuous case: $E_{Fn(Fp)}\left(m_r(x)\right) > E_{Fn(Fp)}\left(m_{c(v)}(x)\right)$, since $m_r(x) < m_{c(v)}(x)$ for given x, corresponding to: $\sigma_{OT}\left(m_r(x)\right) > \sigma_{ET}\left(m_{c(v)}(x)\right)$. In our recent work[1], all the electrical-and-thermoelectric properties were investigated for this discontinuous case.

Some optical coefficients, obtained in Equations (18, 19b-19d, 20a-20d) for given $\left(N, r_{d(a)}, x, T\right)$ -physical conditions, are reported in the following Table 3, in which $\sigma_{OT} > \sigma_{ET}$.

Table 3: Here, some optical coefficients, for some particular values of E, are given as follows.

E in eV	$\sigma_O(E)$	$\kappa_O(E)$	$\varepsilon_{2O}(E)$	$\propto_O(E)$
$E_{gn1(gp1)}$	0	0	0	0
$[E_{gn1(gp1)} + E_{Fn(Fp)}]$	σ_{OT}	κ_{OT}	ε_{2OT}	$\propto_{OT}$
$E \to \infty$	$\frac{q^2\times H}{\pi\times\hbar}$ =Constant	0	0	$\frac{4q^2\times H}{\hbar c n_\infty\times\varepsilon_{free\ space}}$=Constant

E in eV	$\sigma_E(E)$	$\kappa_E(E)$	$\varepsilon_{2E}(E)$	$\propto_E(E)$
$E_{gn2(gp2)}$	0	0	0	0
$[E_{gn2(gp2)} + E_{Fn(Fp)}]$	σ_{ET}	κ_{ET}	ε_{2ET}	$\propto_{ET}$
$E \to \infty$	$\frac{q^2\times H}{\pi\times\hbar}$ =Constant	0	0	$\frac{4q^2\times H}{\hbar c n_\infty\times\varepsilon_{free\ space}}$=Constant

Therefore, for given $[N, r_{d(a)}, x, T]$, all the numerical results of $[\sigma_o(E), \kappa_o(E), \varepsilon_{2o}(E)$, and $\propto_o(E)]$, due to the OP and those of $[\sigma_E(E), \kappa_E(E), \varepsilon_{2,E}(E)$, and $\propto_E(E)]$, due to the E-OP, being determined respectively from Equations (18, 19b-19d], for any E, could thus be used to explain all their corresponding past-or-future experimental results.

ELECTRICAL-AND-THERMOELECTRIC PROPERTIES $[m^*_{n(p)} \equiv m_{c(v)}(x)[m_r(x)]]$

Here, if denoting, for majority electrons (holes), the thermal conductivity by $\sigma_{Th.ET[OT]}(N, r_{d(a)}, x, T)$ in $\frac{W}{cm \times K}$, and the Lorenz number L by: $L = \frac{\pi^2}{3} \times \left(\frac{k_B}{q}\right)^2 = 2.4429637 \left(\frac{W \times ohm}{K^2}\right) = 2.4429637 \times 10^{-8} (V^2 \times K^{-2})$, then the well-known Wiedemann-Frank law states that the ratio, $\frac{\sigma_{Th.ET[OT]}}{\sigma_{ET[OT]}}$, due to the (E-OP and OP) transition, respectively, is proportional to the temperature T(K), as:

$$\frac{\sigma_{Th.ET[OT]}(N, r_{d(a)}, x, T)}{\sigma_{ET[OT]}(N, r_{d(a)}, x, T)} = L \times T. \tag{21}$$

Further, the resistivity is found to be given by: $\rho_{ET[OT]}(N, r_{d(a)}, x, T) \equiv 1/\sigma_{ET[OT]}(N, r_{d(a)}, x, T)$, noting again that $N^* \equiv N - N_{CDn(NDp)}(r_{d(a)}, x)$.

In Eq. (20), one notes that at T= 0 K, $\sigma_{ET[OT]}(N, r_{d(a)}, x, T = 0K)$ is proportional to $E^2_{Fno(Fpo)}$, or to $(N^*)^{\frac{4}{3}}$. Thus, from Eq. (21), one has: $\sigma_{ET[OT]}(N = N_{CDn(NDp)}, r_{d(a)}, x, T = 0K) = 0$ and also $\sigma_{Th.ET[OT]}(N = N_{CDn(NDp)}, r_{d(a)}, x, T = 0K) = 0$ at $N^* = 0$, at which the MIT occurs.

Electrical Coefficients

The relaxation time $\tau_{ET[OT]}$ is related to $\sigma_{ET[OT]}$ by[1]:

$\tau_{ET[OT]}(N, r_{d(a)}, x, T) \equiv \sigma_{ET[OT]}(N, r_{d(a)}, x, T) \times \frac{m^*_{n(p)}(x) \times m_o}{q^2 \times (N^*/g_{c(v)})}$. Therefore, the mobility $\mu_{ET[OT]}$ is given by:

$$\mu_{ET[OT]}(N, r_{d(a)}, x, T) \equiv \mu_{ET[OT]}(N^*, r_{d(a)}, T) = \frac{q \times \tau_{ET[OT]}(N, r_{d(a)}, x, T)}{m^*_{n(p)}(x) \times m_o} = \frac{\sigma_{ET[OT]}(N, r_{d(a)}, x, T)}{q \times (N^*/g_{c(v)})} \left(\frac{cm^2}{V \times s}\right). \tag{22}$$

Here, at T= 0K, $\mu_{ET[OT]}(N^*, r_{d(a)}, T)$ is thus proportional to $(N^*)^{1/3}$, since $\sigma_{ET[OT]}(N^*, r_{d(a)}, T = 0K)$ is proportional to $(N^*)^{4/3}$. Thus,

$\tau_{ET[OT]}(N^* = 0, r_{d(a)}, T = 0K) = 0$ and $\mu_{ET[OT]}(N^* = 0, r_{d(a)}, T = 0K) = 0$ at $N^* = 0$, at which the MIT occurs.

Then, the Hall factor is defined by:

$r_{HET[OT]}(N, r_{d(a)}, x, T) \equiv \frac{\langle \tau_{ET[OT]}{}^2 \rangle_{FDDF}}{[\langle \tau_{ET[OT]} \rangle_{FDDF}]^2} = \frac{G_4(y)}{[G_2(y)]^2}$, $y \equiv \frac{\pi}{\xi_{n(p)}(N, r_{d(a)}, x, T)} = \frac{\pi k_B T}{E_{Fn(Fp)}(N, r_{d(a)}, x, T)}$, and therefore, the Hall mobility yields:

$$\mu_{HET[OT]}(N, r_{d(a)}, x, T) \equiv \mu_{ET[OT]}(N, r_{d(a)}, x, T) \times r_{HET[OT]}(N^*, T) \left(\frac{cm^2}{V \times s}\right), \qquad (23)$$

Noting that, at T=0K, since $r_{HET[OT]}(N, r_{d(a)}, x, T) = 1$, one therefore gets: $\mu_{HET[OT]}(N, r_{d(a)}, x, T) \equiv \mu_{ET[OT]}(N, r_{d(a)}, x, T)$.

Our generalized Einstein relation

Our generalized Einstein relation is found to be defined as[1]:

$$\frac{D_{ET[OT]}(N, r_{d(a)}, x, T)}{\mu_{ET[OT]}(N, r_{d(a)}, x, T)} \equiv \frac{N^*}{q} \times \frac{dE_{Fn(Fp)}}{dN^*} \equiv \frac{k_B \times T}{q} \times \left(u \frac{d\xi_{n(p)}(u)}{du}\right) = \sqrt{\frac{3 \times L}{\pi^2}} \times T \times \left(u \frac{d\xi_{n(p)}(u)}{du}\right), \frac{k_B}{q} = \sqrt{\frac{3 \times L}{\pi^2}}, \qquad (24)$$

Where $D_{ET[OT]}(N, r_{d(a)}, x, T)$ is the diffusion coefficient, $\xi_{n(p)}(u)$ is defined in Eq. (11), and the mobility $\mu_{ET[OT]}(N, r_{d(a)}, x, T)$ is determined in Eq. (22). Then, by differentiating this function $\xi_{n(p)}(u)$ with respect to u, one thus obtains $\frac{d\xi_{n(p)}(u)}{du}$. Therefore, Eq. (17) can also be rewritten as:

$$\frac{D_{ET[OT]}(N, r_{d(a)}, x, T)}{\mu_{ET[OT]}(N, r_{d(a)}, x, T)} = \frac{k_B \times T}{q} \times u \frac{V'(u) \times W(u) - V(u) \times W'(u)}{W^2(u)},$$

Where $W'(u) = ABu^{B-1}$ and $V'(u) = u^{-1} + 2^{-\frac{3}{2}} e^{-du}(1 - du) + \frac{2}{3} A u^{B-1} F(u) \left[\left(1 + \frac{3B}{2}\right) + \frac{4}{3} \times \frac{bu^{-\frac{4}{3}} + 2cu^{-\frac{8}{3}}}{1 + bu^{-\frac{4}{3}} + cu^{-\frac{8}{3}}}\right]$.

One remarks that: (i) as $u \to 0$, one has: $W^2 \simeq 1$ and $u[V' \times W - V \times W'] \simeq 1$, and therefore: $\frac{D_{n(p)}(u)}{\mu} \simeq \frac{k_B \times T}{q}$, and (ii) as $u \to \infty$, one has: $W^2 \approx A^2 u^{2B}$ and $u[V' \times W - V \times W'] \approx \frac{2}{3} a u^{2/3} A^2 u^{2B}$, and therefore, in this **highly degenerate case** and at T=0K, the **above generalized Einstein relation** is reduced to the **usual Einstein one**: $\frac{D_{ET[OT]}(N, r_{d(a)}, x, T)}{\mu_{ET[OT]}(N, r_{d(a)}, x, T)} \approx \frac{2}{3} E_{Fno(Fpo)}(N^*)/q$. In other words, **Eq. (24) verifies the correct limiting conditions**.

Furthermore, in the present degenerate case ($u \gg 1$), Eq. (24) gives:

$$\frac{D_{ET[OT]}(N, r_{d(a)}, x, T)}{\mu_{ET[OT]}(N, r_{d(a)}, x, T)} \simeq \frac{2}{3} \times \frac{E_{Fno(Fpo)}(u)}{q} \times \left[1 + \frac{4}{3} \times \frac{\left(bu^{-\frac{4}{3}} + 2cu^{-\frac{8}{3}}\right)}{\left(1 + bu^{-\frac{4}{3}} + cu^{-\frac{8}{3}}\right)}\right],$$

Where $a = [3\sqrt{\pi}/4]^{2/3}$, $b = \frac{1}{8}\left(\frac{\pi}{a}\right)^2$ and $c = \frac{62.3739855}{1920}\left(\frac{\pi}{a}\right)^4$.

Thermoelectric Coefficients

Here, as noted above, $E_{Fn(Fp)}(m_r(x)) > E_{Fn(Fp)}\left(m_{c(v)}(x)\right)$ or $\xi_{n(p)}(m_r(x)) > \xi_{n(p)}\left(m_{c(v)}(x)\right)$ for a given T, since $m_r(x) < m_{c(v)}(x)$ for given x, corresponding to: $\sigma_{OT}(m_r(x)) > \sigma_{ET}\left(m_{c(v)}(x)\right)$.

Then, from Eq. (20a), obtained for $\sigma_{ET[OT]}(N, r_{d(a)}, x, T)$, the well-known Mott definition for the thermoelectric power or for the Seebeck coefficient, $S_{ET[OT]}$, is found to be given by:

$$S_{ET[OT]}(N, r_{d(a)}, x, T) \equiv \frac{-\pi^2}{3} \times \frac{k_B}{q>0} \times k_B T \times \left.\frac{\partial \ln \sigma_{ET[OT]}}{\partial E}\right]_{E=E_{Fn(Fp)}} = \frac{-\pi^2}{3} \times \frac{k_B}{q} \times \frac{\partial \ln \sigma_{ET[OT]}(\xi_{n(p)})}{\partial \xi_{n(p)}}.$$

Then, using Eq. (11), for the degenerate case, $\xi_{n(p)} \geq 0$, one gets, by putting

$$F_{SbET[OT]}(N, r_{d(a)}, x, T) \equiv \left[1 - \frac{y^2}{3 \times G_2\left(y = \frac{\pi}{\xi_{n(p)}}\right)}\right],$$

$$S_{ET[OT]}(N, r_{d(a)}, x, T) \equiv \frac{-\pi^2}{3} \times \frac{k_B}{q} \times \frac{2F_{SbET[OT]}(N^*, T)}{\xi_{n(p)}} = -\sqrt{\frac{3 \times L}{\pi^2}} \times \frac{2 \times \xi_{n(p)}}{\left(1 + \frac{3 \times \xi_{n(p)}^2}{\pi^2}\right)} = -2\sqrt{L} \times \frac{\sqrt{ZT_{ET[OT]Mott}}}{1 + ZT_{ET[OT]Mott}}\left(\frac{V}{K}\right) < 0, \quad ZT_{ET[OT]Mott} = \frac{\pi^2}{3 \times \xi_{n(p)}^2} \quad , \qquad (25)$$

according to:

$$\frac{\partial S_{ET[OT]}}{\partial \xi_{n(p)}} = \sqrt{\frac{3 \times L}{\pi^2}} \times 2 \times \frac{\frac{3 \times \xi_{n(p)}^2}{\pi^2} - 1}{\left(1 + \frac{3 \times \xi_{n(p)}^2}{\pi^2}\right)^2} = \sqrt{\frac{3 \times L}{\pi^2}} \times 2 \times \frac{ZT_{ET[OT]Mott} \times [1 - ZT_{ET[OT]Mott}]}{[1 + ZT_{ET[OT]Mott}]^2}.$$

Here, one notes that: (i) as $\xi_{n(p)} \to +\infty$ or $\xi_{n(p)} \to +0$, one has a same limiting value of $S_{ET[OT]}$: $S_{ET[OT]} \to -0$, (ii) at $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}} \simeq 1.8138$, since $\frac{\partial S_{ET[OT]}}{\partial \xi_{n(p)}} = 0$, one therefore gets: a minimum $\left(S_{ET[OT]}\right)_{min.} = -\sqrt{L} \simeq -1.563 \times 10^{-4} \left(\frac{V}{K}\right)$, and (iii) at $\xi_{n(p)} = 1$ one obtains: $S_{ET[OT]} \simeq -1.322 \times 10^{-4} \left(\frac{V}{K}\right)$.

Further, the figure of merit, ZT, is found to be defined by:

$$\mathrm{ZT}_{\mathrm{ET[OT]}}\left(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}\right) \equiv \frac{\mathrm{S}^2 \times \sigma_{\mathrm{E}} \times \mathrm{T}}{\kappa} = \frac{\mathrm{S}^2}{\mathrm{L}} = \frac{4 \times \mathrm{ZT}_{\mathrm{ET[OT]Mott}}}{\left[1 + \mathrm{ZT}_{\mathrm{ET[OT]Mott}}\right]^2}. \tag{26}$$

Here, one notes that: (i) $\frac{\partial(\mathrm{ZT}_{\mathrm{ET[OT]}})}{\partial \xi_{\mathrm{n(p)}}} = 2 \times \frac{\mathrm{S}_{\mathrm{ET[OT]}}}{\mathrm{L}} \times \frac{\partial \mathrm{S}_{\mathrm{ET[OT]}}}{\partial \xi_{\mathrm{n(p)}}}$, $\mathrm{S}_{\mathrm{ET[OT]}} < 0$, (ii) at $\xi_{\mathrm{n(p)}} = \sqrt{\frac{\pi^2}{3}} \simeq 1.8138$, since $\frac{\partial(\mathrm{ZT}_{\mathrm{ET[OT]}})}{\partial \xi_{\mathrm{n(p)}}} = 0$, one gets: a maximum $\left(\mathrm{ZT}_{\mathrm{ET[OT]}}\right)_{\mathrm{max.}} = 1$, and $\mathrm{ZT}_{\mathrm{ET[OT]Mott}} = 1$, and (iii) at $\xi_{\mathrm{n(p)}} = 1$, one obtains: $\mathrm{ZT}_{\mathrm{ET[OT]}} \simeq 0.715$ and $\mathrm{ZT}_{\mathrm{ET[OT]Mott}} = \frac{\pi^2}{3} \simeq 3.290$.

Finally, the first Van-Cong coefficient, $\mathrm{VC1}_{\mathrm{ET[OT]}}$, can be defined by:

$$\mathrm{VC1}_{\mathrm{ET[OT]}}\left(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}\right) \equiv -\mathrm{N}^* \times \frac{d\,\mathrm{S}_{\mathrm{ET[OT]}}}{d\mathrm{N}^*}\left(\frac{\mathrm{V}}{\mathrm{K}}\right) = \mathrm{N}^* \times \frac{\partial\,\mathrm{S}_{\mathrm{ET[OT]}}}{\partial\,\xi_{\mathrm{n(p)}}} \times -\frac{\partial\,\xi_{\mathrm{n(p)}}}{\partial\,\mathrm{N}^*}, \tag{27}$$

being equal to 0 for $\xi_{\mathrm{n(p)}} = \sqrt{\frac{\pi^2}{3}}$,

and the second Van-Cong coefficient, $\mathrm{VC2}_{\mathrm{ET[OT]}}$, as:

$$\mathrm{VC2}_{\mathrm{ET[OT]}}\left(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}\right) \equiv \mathrm{T} \times \mathrm{VC1}_{\mathrm{ET[OT]}}\ (\mathrm{V}), \tag{28}$$

the Thomson coefficient, Ts , by:

$$\mathrm{Ts}_{\mathrm{ET[OT]}}\left(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}\right) \equiv \mathrm{T} \times \frac{d\,\mathrm{S}_{\mathrm{ET[OT]}}}{d\mathrm{T}}\left(\frac{\mathrm{V}}{\mathrm{K}}\right) = \mathrm{T} \times \frac{\partial\,\mathrm{S}_{\mathrm{ET[OT]}}}{\partial \xi_{\mathrm{n(p)}}} \times \frac{\partial \xi_{\mathrm{n(p)}}}{\partial \mathrm{T}}, \tag{29}$$

being equal to 0 for $\xi_{\mathrm{n(p)}} = \sqrt{\frac{\pi^2}{3}}$,

and the Peltier coefficient, $\mathrm{Pt}_{\mathrm{ET[OT]}}$, as:

$$\mathrm{Pt}_{\mathrm{ET[OT]}}\left(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}\right) \equiv \mathrm{T} \times \mathrm{S}_{\mathrm{ET[OT]}}\ (\mathrm{V}). \tag{30}$$

One notes here that for given physical conditions N (or T) and for the decreasing $\xi_{\mathrm{n(p)}}$, since $\mathrm{VC1}_{\mathrm{ET[OT]}}\left(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}\right)$ and $\mathrm{Ts}_{\mathrm{ET[OT]}}\left(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}\right)$ are expressed in terms of $\frac{-d\,\mathrm{S}_{\mathrm{ET[OT]}}}{d\mathrm{N}^*}$ and $\frac{d\,\mathrm{S}_{\mathrm{ET[OT]}}}{d\mathrm{T}}$, one has: $[\mathrm{VC1}_{\mathrm{ET[OT]}}, \mathrm{Ts}_{\mathrm{ET[OT]}}] < 0$ for $\xi_{\mathrm{n(p)}} > \sqrt{\frac{\pi^2}{3}}$, $[\mathrm{VC1}_{\mathrm{ET[OT]}}, \mathrm{Ts}_{\mathrm{ET[OT]}}] = 0$ for $\xi_{\mathrm{n(p)}} = \sqrt{\frac{\pi^2}{3}}$, and $[\mathrm{VC1}_{\mathrm{ET[OT]}}, \mathrm{Ts}_{\mathrm{ET[OT]}}] > 0$ for $\xi_{\mathrm{n(p)}} < \sqrt{\frac{\pi^2}{3}}$, stating also that for $\xi_{\mathrm{n(p)}} = \sqrt{\frac{\pi^2}{3}}$:

(i) $S_{ET[OT]}$, determined in Eq. (25), thus presents **a same minimum** $\left(S_{ET[OT]}\right)_{min.} = -\sqrt{L} \simeq -1.563 \times 10^{-4} \left(\frac{V}{K}\right)$,

(ii) $ZT_{ET[OT]}$, determined in Eq. (26), therefore presents **a same maximum:** $\left(ZT_{ET[OT]}\right)_{max.} = 1$, since the variations of $ZT_{ET[OT]}$ are expressed in terms of $[VC1_{ET[OT]}, Ts_{ET[OT]}] \times S_{ET[OT]}$, $S_{ET[OT]} < 0$.

Furthermore, it is interesting to remark that the $VC2_{ET[OT]}$-coefficient is related to our generalized Einstein relation (24) by:

$$\frac{k_B}{q} \times VC2_{ET[OT]}\left(N, r_{d(a)}, x, T\right) \equiv -\frac{\partial\, S_{ET[OT]}}{\partial \xi_{n(p)}} \times \frac{D_{ET[OT]}\left(N, r_{d(a)}, x, T\right)}{\mu_{ET[OT]}\left(N, r_{d(a)}, x, T\right)} \left(\frac{V^2}{K}\right), \quad \frac{k_B}{q} = \sqrt{\frac{3 \times L}{\pi^2}}, \tag{31}$$

according, in this work, with the use of our Eq. (25), to:

$$VC2_{ET[OT]}\left(N, r_{d(a)}, x, T\right) \equiv -\frac{D_{ET[OT]}\left(N, r_{d(a)}, x, T\right)}{\mu_{ET[OT]}\left(N, r_{d(a)}, x, T\right)} \times 2 \times \frac{ZT_{ET[OT]Mott} \times [1 - ZT_{ET[OT]Mott}]}{[1 + ZT_{ET[OT]Mott}]^2} \ (V).$$

Of course, our relation (31) is reduced to: $\frac{D_{ET[OT]}}{\mu_{ET[OT]}}$, $VC1_{ET[OT]}$ and $VC2_{ET[OT]}$, being determined respectively by Equations (24, 27, 28). This may be a new result.

CONCLUDING REMARKS

Some important concluding remarks can be repoted as follows.

In the $\mathbf{n^+(p^+) - GaAs(1-x)Te(x)}$ − crystalline alloy, $0 \le x \le 1$, x being the concentration, the optical coefficients, and the electrical-and-thermoelectric laws, relations, and various coefficients, being enhanced by:

(i) our static dielectric constant law, $\varepsilon(r_{d(a)}, x)$, $r_{d(a)}$ being the donor (acceptor) d(a)-radius, given in Equations (1a, 1b),

(ii) our accurate Fermi energy, $E_{Fn(Fp)}$, given in Eq. (11) and accurate with a precision of the order of 2.11×10^{-4} [9], affecting all the expressions of optical, and electrical-and-thermoelectric coefficients,

(iii)our optical-and-electrical transformation duality given in Eq. (15), and finally

(iv)our optical-and-electrical conductivity models, given in Eq. (18, 20a), are now investigated, basing on our physical model, and Fermi-Dirac distribution function, as those given in our recent works.[1, 2]

It should be noted here that for x=0, these obtained numerical results may be reduced to those given in the n(p)-type degenerate **GaAs-crystal**.[3] Then, some important remarks can be repoted as follows.

(1) As observed in Equations (3, 5, 6), the critical impurity density $N_{CDn(CDp)}$, defined by the generalized Mott criterium in the metal-insulator transition (**MIT**), is just the density of electrons (holes), localized in the exponential conduction (valence)-band tail (**EBT**), $N^{EBT}_{CDn(CDp)}$, being obtained with a precision of the order of $\mathbf{2.89 \times 10^{-7}}$, respectively, as given in our recent works.[3] Therefore, the effective electron (hole)-density can be defined as: $N^* \equiv N - N_{CDn(CDp)} \simeq N - N^{EBT}_{CDn(CDp)}$, N being the total impurity density, as that observed in the compensated crystals.

(2) The ratio of the inverse effective screening length $k_{sn(sp)}$ to Fermi wave number $k_{Fn(kp)}$ at 0 K, $R_{sn(sp)}(N^*)$, defined in Eq. (7), is valid at any N^*.

(3) From Equations (20a, 21-30), for any given x, $r_{d(a)}$ and N (or T), with increasing T (or decreasing N), one obtains: (i) for $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}} \simeq 1.8138$, while the numerical results of the Seebeck coefficient $S_{ET[OT]}$ present a same minimum $\left(S_{ET[OT]}\right)_{min.}$ $\left(\simeq -1.563 \times 10^{-4} \frac{V}{K}\right)$, those of the figure of merit $ZT_{ET[OT]}$ show a same maxi**mum** $\left(ZT_{ET[OT]}\right)_{max.} = 1$, (ii) for $\xi_{n(p)} = 1$, the numerical results of $S_{ET[OT]}$, $ZT_{ET[OT]}$, the Mott figure of merit $ZT_{ET[OT]Mott}$, the first Van-Cong coefficient $VC1_{ET[OT]}$, and the Thomson coefficient $Ts_{ET[OT]}$, present the same results: $-1.322 \times 10^{-4} \frac{V}{K}$, 0.715, 3.290, $1.105 \times 10^{-4} \frac{V}{K}$, and $1.657 \times 10^{-4} \frac{V}{K}$, respectively, and finally (iii) for $\xi_{n(p)} = \sqrt{\frac{\pi^2}{3}} \simeq 1.8138$, $ZT_{ET[OT]Mott} = 1$, as those given in our recent work.[1] It seems that these same results could represent **a new law in the thermoelectric properties, obtained in the degenerate case ($\xi_{n(p)} \geq 0$).**

(4) Further, our electrical-and-thermoelectric relation is given in Eq. (31) by: $\frac{k_B}{q} \times VC2_{ET[OT]}\left(N, r_{d(a)}, x, T\right) \equiv -\frac{\partial S_{ET[OT]}}{\partial \xi_{n(p)}} \times \frac{D_{ET[OT]}(N, r_{d(a)}, x, T)}{\mu_{ET[OT]}(N, r_{d(a)}, x, T)} \left(\frac{V^2}{K}\right)$, $\frac{k_B}{q} = \sqrt{\frac{3 \times L}{\pi^2}}$, according, in this work, to:

$\mathrm{VC2}_{\mathrm{ET[OT]}}(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}) \equiv -\frac{\mathrm{D}_{\mathrm{ET[OT]}}(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T})}{\mu_{\mathrm{ET[OT]}}(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T})} \times 2 \times \frac{\mathrm{ZT}_{\mathrm{ET[OT]Mott}} \times [1 - \mathrm{ZT}_{\mathrm{ET[OT]Mott}}]}{[1 + \mathrm{ZT}_{\mathrm{ET[OT]Mott}}]^2}$ (V), being reduced to: $\frac{\mathrm{D}_{\mathrm{ET[OT]}}}{\mu_{\mathrm{ET[OT]}}}$, $\mathrm{VC1}_{\mathrm{ET[OT]}}$ and $\mathrm{VC2}_{\mathrm{ET[OT]}}$, determined respectively in Equations (24, 27, 28). This can be **a new result**.

(5) Finally, for given $[\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T}]$, all the numerical results of $[\sigma_{\mathrm{O}}(\mathrm{E}), \kappa_{\mathrm{O}}(\mathrm{E}), \varepsilon_{2\mathrm{O}}(\mathrm{E})$, and $\propto_{\mathrm{O}}(\mathrm{E})]$, given in the OP, and those of $[\sigma_{\mathrm{E}}(\mathrm{E}), \kappa_{\mathrm{E}}(\mathrm{E}), \varepsilon_{2\mathrm{E}}(\mathrm{E})$, and $\propto_{\mathrm{E}}(\mathrm{E})]$, given in the E-OP, being determined respectively from Equations (18, 19b-19d], for any E, could thus be used to explain all their corresponding past-or-future experimental results. Therefore, this can also be explained for $\sigma_{\mathrm{ET[OT]}}(\mathrm{N}, \mathrm{r}_{\mathrm{d(a)}}, \mathrm{x}, \mathrm{T})$, obtained in Eq. (20a) for the (OP − [E-OP])-transition, and their derived electrical-and-thermoelectric results given in Equations (21-31).

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